### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- · Logic-level compatible
- Very fast switching
- Trench MOSFET technology

## 3. Applications

- · Relay driver
- · High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	60	V		
V <sub>GS</sub>	gate-source voltage			-20	-	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	350	mA		
Static characte	Static characteristics (per transistor)								
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.01; $T_{j}$ = 25 °C		-	1	1.6	Ω		

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



60 V, 350 mA dual N-channel Trench MOSFET

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	6 5 4	D1 D2
2	G1	gate1		
3	D2	drain2		(
4	S2	source2	0	
5	G2	gate2	1 2 3	
6	D1	drain1	SOT666	017aaa254

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
2N7002PV	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	SOT666		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
2N7002PV	ZF

#### 60 V, 350 mA dual N-channel Trench MOSFET

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		'			
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	350	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	250	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	1.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	330	mW
			[1]	-	390	mW
		T <sub>sp</sub> = 25 °C		-	1090	mW
Per device			'			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode			1		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	350	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

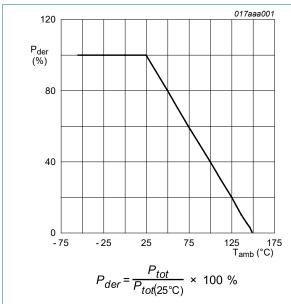


Fig. 1. Normalized total power dissipation as a function of ambient temperature

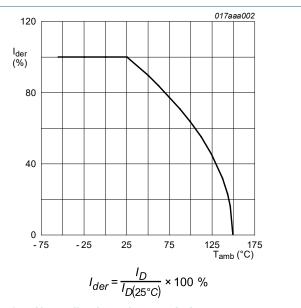
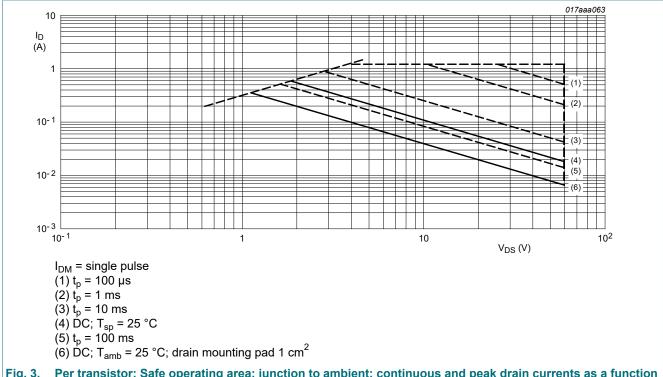


Fig. 2. Normalized continuous drain current as a function of ambient temperature

#### 60 V, 350 mA dual N-channel Trench MOSFET



#### 60 V, 350 mA dual N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device	,						_
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
Per transist	tor						_
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	330	380	K/W
	junction to ambient		[2]	-	280	320	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

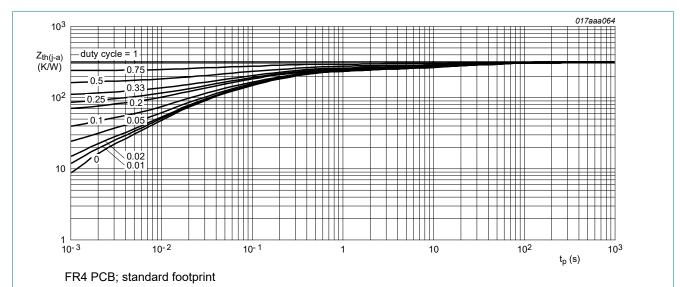


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

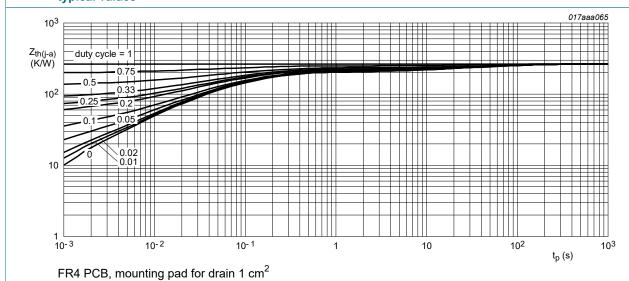


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002PV

### 60 V, 350 mA dual N-channel Trench MOSFET

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 5 V; $I_{D}$ = 50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.01; $T_{j}$ = 25 °C	-	1.3	2	Ω
		$V_{GS}$ = 10 V; $I_{D}$ = 500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.01; $T_{j}$ = 25 °C	-	1	1.6	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.01; $T_{j}$ = 25 °C	-	400	-	mS
Dynamic ch	aracteristics (per transist	or)	'			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 300 mA; V <sub>GS</sub> = 4.5 V;	-	0.6	0.8	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	30	50	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	3	6	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	10	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	in diode (per transistor)		•			
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.75	1.1	V

#### 60 V, 350 mA dual N-channel Trench MOSFET

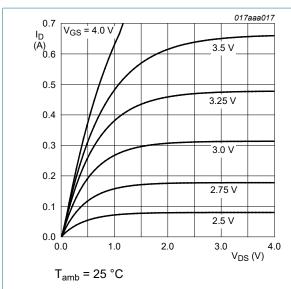
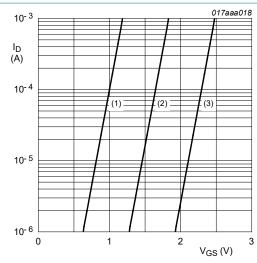


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

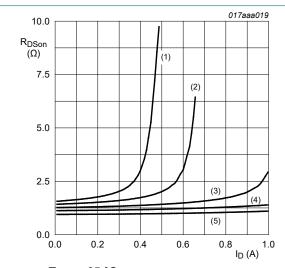


 $T_{amb}$  = 25 °C;  $V_{DS}$  = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



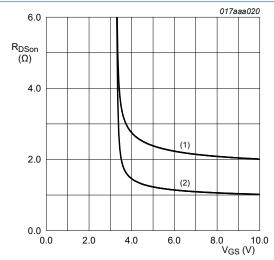
 $T_{amb}$  = 25 °C

(1)  $V_{GS} = 3.25 \text{ V}$ 

 $(2) V_{GS} = 3.5 V$ 

(3)  $V_{GS} = 4 V$ (4)  $V_{GS} = 5 V$  $(5) V_{GS} = 10 V$ 

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 500 \text{ mA}$ 

(1) T<sub>amb</sub> = 150 °C

 $(2) T_{amb} = 25 °C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 60 V, 350 mA dual N-channel Trench MOSFET

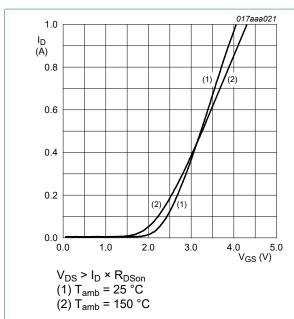
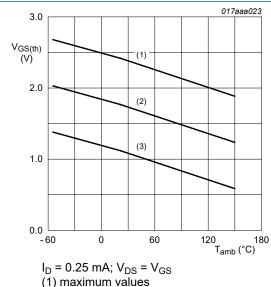


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



(1) maximum values

- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature

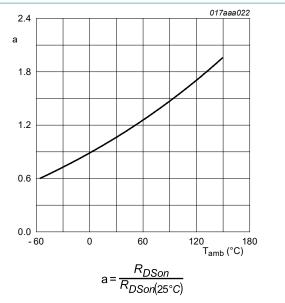
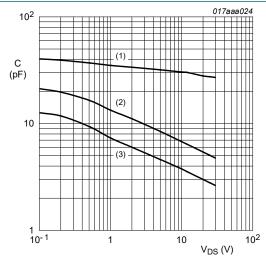


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 60 V, 350 mA dual N-channel Trench MOSFET

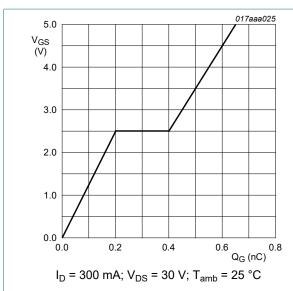


Fig. 14. Gate-source voltage as a function of gate charge; typical values

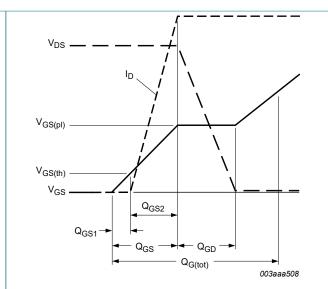
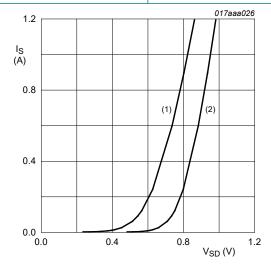


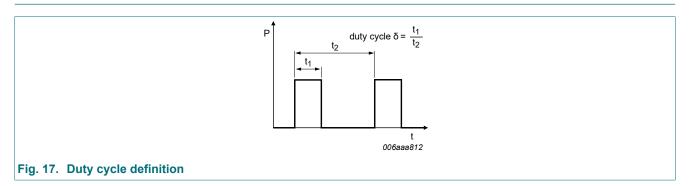
Fig. 15. Gate charge waveform definitions



V<sub>GS</sub> = 0 V (1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information



#### 60 V, 350 mA dual N-channel Trench MOSFET

# 12. Package outline

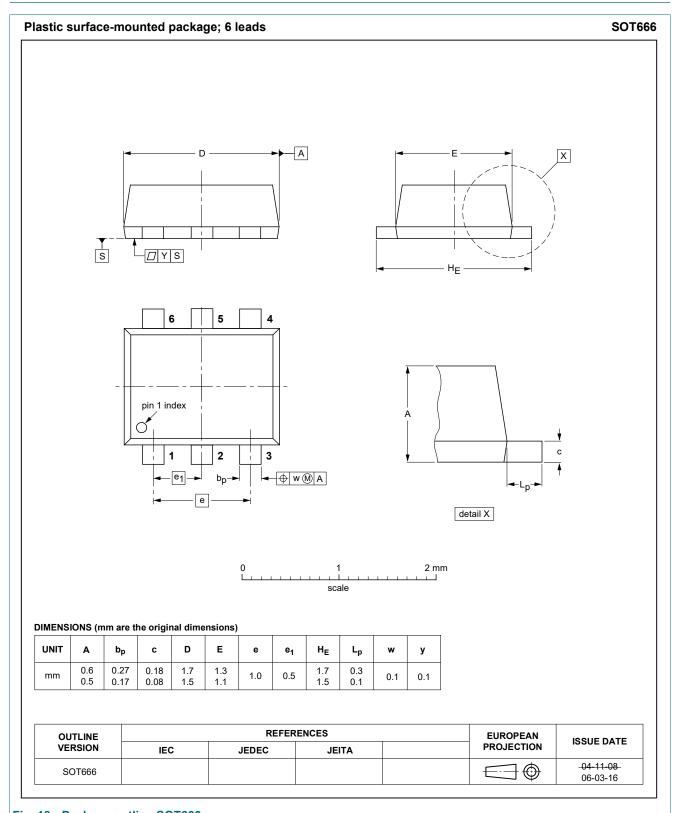
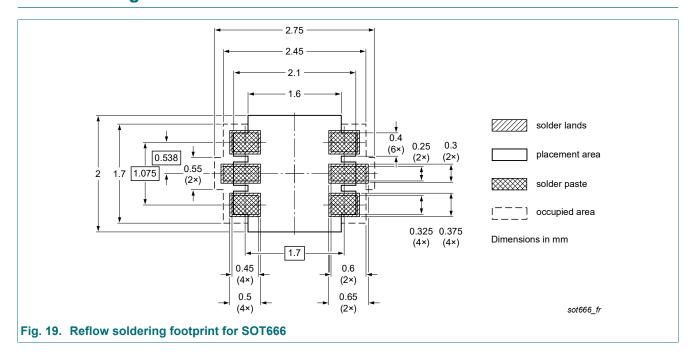


Fig. 18. Package outline SOT666

#### 60 V, 350 mA dual N-channel Trench MOSFET

# 13. Soldering



### 60 V, 350 mA dual N-channel Trench MOSFET

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
2N7002PV v.3	20221228	Product data sheet	-	2N7002PV v.2			
Modifications:	Product chang	Product changed to non-automotive qualification					
2N7002PV v.2	20201123	Product data sheet	-	2N7002PV v.1			
2N7002PV v.1	20100805	Product data sheet	-	-			

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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